

Erratum: Self-Diffusion in Amorphous Silicon
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In our Letter, the preexponential factor D_0 for the self-diffusion in amorphous silicon as derived from neutron reflectometry and SIMS data [see Eq. (2) in the Letter] was given incorrectly. The correct preexponential factor is 1.5×10^4 m²/s, exactly a factor of 10 lower than the erroneous value given before. The corresponding error of $\log_{10} D_0 = 1.5$ remains unchanged, as does the calculated activation energy. Consequently, the entropy of diffusion was recalculated to $\Delta S \approx 24 k_B$.

There is no effect at all on the interpretation of the data and on the conclusion.

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